Claim rejection under 35 USC 112

The following is a quotation of the first paragraph of 35 U.S.C. 112(a):

(a) IN GENERAL.—The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains,or with which it is most nearly connected, to make and use the same, and shall set forth the best mode contemplated by the inventor or joint inventor of carrying out the invention.

The following is a quotation of 35 U.S.C. 112(b):

(b) CONCLUSION.—The specification shall conclude with one or more claims particularly pointing out and distinctlyclaiming the subject matter which the inventor or a joint inventor regards as the invention.  
The following is a quotation of 35 U.S.C. 112 (pre-AIA), second paragraph:The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1-19 are rejected under 35 U.S.C. 112(b) or 35 U.S.C. 112 (pre-AIA),second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which the inventor or a joint inventor,

**Regarding claim 1**. A semiconductor device that converts DC power to AC power, the semiconductor device comprising:  
an insulating substrate; a first conductive part provided on the insulating substrate so as to extend in a first direction; a second conductive part provided on the insulating substrate so as to be separated from the first conductive part in a second direction different from the first direction and to extend in the first direction; a plurality of third conductive parts provided on the insulating substrate so as to be lined along the first direction between the first conductive part and the second conductive part; a plurality of first switches mounted on the first conductive part along the first direction, and each provided with a first main electrode, a second main electrode and a control electrode, the first main electrode being electrically connected to the first conductive part; a plurality of second switches each mounted on the corresponding third conductive part, and each provided with a third main electrode, a fourth main electrode and a control electrode, the third main electrode being electrically connected to the second main electrode of the first switch, the fourth main electrode being electrically connected to the second conductive part; a plurality of signal terminals arrayed along the first direction so that the first conductive part is positioned between the signal terminals and the third conductive parts; a power supply terminal electrically connected to the first conductive part, and arranged on one end side of the insulating substrate where the plurality of signal terminals are provided; a ground terminal electrically connected to the second conductive part, and arranged on the one end side of the insulating substrate; and a plurality of output terminals each electrically connected to the corresponding third conductive part, arrayed along the first direction on the other end side which is an opposite side of the one end side of the insulating substrate, and provided over a straight line that passes through the second conductive part and extends in the first direction.   
   
**Regarding claim 2**. The semiconductor device according to claim 1, wherein the fourth main electrode of the second switch and the second conductive part are electrically connected by a conductive wire, and the conductive wire has one end connected to the fourth main electrode and has the other end connected to an area between the output terminals that are adjacent to each other in the second conductive part.   
   
**Regarding claim 3**. The semiconductor device according to claim 1, wherein tips of the plurality of signal terminals are arranged zigzag along the first direction.   
   
**Regarding claim 4**. The semiconductor device according to claim 3, wherein tips of the power supply terminal and the ground terminal are arranged zigzag to the plurality of signal terminals.   
   
**Regarding claim 5**. The semiconductor device according to claim 1, wherein at least one of the power supply terminal, the ground terminal and the output terminals has a planar shape that avoids a conductive part provided on a corner of the insulating substrate.   
   
**Regarding claim 6**. The semiconductor device according to claim 5, wherein the planar shape is an L shape.   
   
**Regarding claim 7**. A manufacturing method of a semiconductor device that converts DC power to AC power, the manufacturing method comprising:  
preparing a wiring board having an insulating substrate, a first conductive part provided on the insulating substrate so as to extend in a first direction, a second conductive part provided on the insulating substrate so as to be separated from the first conductive part in a second direction different from the first direction and to extend in the first direction, and a plurality of third conductive parts provided on the insulating substrate so as to be lined along the first direction between the first conductive part and the second conductive part; preparing a lead frame having a first terminal group including a plurality of signal terminals, a power supply terminal and a ground terminal, and a second terminal group including a plurality of output terminals; mounting a plurality of first switches on the first conductive part along the first direction with cream solder interposed therebetween, and mounting second switches on the individual third conductive parts with cream solder interposed therebetween; positioning the wiring board and the lead frame so that a base of the power supply terminal, a base of the ground terminal, and bases of the output terminals are respectively in contact on the first conductive part, on a fourth conductive part which is connected to the second conductive part and extending in the second direction, and on the third conductive parts, with cream solder interposed therebetween; joining the power supply terminal, the ground terminal and the output terminals to the first conductive part, the second conductive part and the third conductive parts, respectively, by reflow processing; and bonding the second conductive part and the main electrode of the second switch by a conductive wire.   
   
**Regarding claim 8**. The manufacturing method of the semiconductor device according to claim 7, wherein the bonding includes first connection of connecting one end of the conductive wire to the main electrode of the second switch, and second connection of connecting the other end of the conductive wire to an area between the output terminals that are adjacent to each other in the second conductive part, after the first connection.